

Fei Xue

List of Publications by Year in descending order

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all docs

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33
times ranked

659
citing authors

#	ARTICLE	IF	CITATIONS
1	Resistive switching characteristics and mechanisms in silicon oxide memory devices. ChemistrySelect, 2016, 1, .	0.7	2
2	Electroforming and resistive switching in silicon dioxide resistive memory devices. RSC Advances, 2015, 5, 21215-21236.	1.7	59
3	Nonplanar InGaAs Gate Wrapped Around Field-Effect Transistors. IEEE Transactions on Electron Devices, 2014, 61, 2332-2337.	1.6	16
4	III-V Gate-wrap-around field-effect-transistors with high-k gate dielectrics. , 2014, , .		3
5	Oxygen-induced bi-modal failure phenomenon in SiO _x -based resistive switching memory. Applied Physics Letters, 2013, 103, 033521.	1.5	30
6	Effects of sidewall etching on electrical properties of SiO _x resistive random access memory. Applied Physics Letters, 2013, 103, 213505.	1.5	20
7	Comprehensive trap-level study in SiO _x -based resistive switching memory. , 2013, , .		9
8	Investigation of edge- and bulk-related resistive switching behaviors and backward-scan effects in SiO _x -based resistive switching memory. Applied Physics Letters, 2013, 103, 193508.	1.5	26
9	HfO ₂ dielectrics engineering using low power SF ₆ plasma on InP and In _{0.53} Ga _{0.47} As metal-oxide-semiconductor field-effect-transistors. Applied Physics Letters, 2012, 100, 243508.	1.5	6
10	Effect of hydrogen/deuterium incorporation on electroforming voltage of SiO _x resistive random access memory. Applied Physics Letters, 2012, 101, .	1.5	20
11	Excellent device performance of 3D In _{0.53} Ga _{0.47} As gate-wrap-around field-effect-transistors with high-k gate dielectrics. , 2012, , .		8
12	Sub-50-nm In _{0.7} Ga _{0.3} As MOSFETs With Various Barrier Layer Materials. IEEE Electron Device Letters, 2012, 33, 32-34.	2.2	51
13	Channel Thickness Dependence of InGaAs Quantum-Well Field-Effect Transistors With High- κ Gate Dielectrics. IEEE Electron Device Letters, 2012, 33, 1255-1257.	2.2	10
14	Memory switching properties of e-beam evaporated SiO _x on N ⁺⁺ Si substrate. Applied Physics Letters, 2012, 100, .	1.5	48
15	Tristate Operation in Resistive Switching of SiO ₂ Thin Films. IEEE Electron Device Letters, 2012, 33, 1702-1704.	2.2	25
16	Study of polarity effect in SiO _x -based resistive switching memory. Applied Physics Letters, 2012, 101, 052111.	1.5	47
17	Study of SiO _x -based complementary resistive switching memristor. , 2012, , .		9
18	Effects of SF ₆ plasma treatment on electrical characteristics of TaN-Al ₂ O ₃ -InP metal-oxide-semiconductor field-effect transistor. Applied Physics Letters, 2012, 101, 063505.	1.5	2

#	ARTICLE	IF	CITATIONS
19	Optimization of Fluorine Plasma Treatment for Interface Improvement on HfO ₂ /In _{0.53} Ga _{0.47} As MOSFETs. Applied Sciences (Switzerland), 2012, 2, 233-244.	1.3	6
20	Physical and Electrical Analysis of Post-HfO ₂ Fluorine Plasma Treatment for the Improvement of In _{0.53} Ga _{0.47} As MOSFETs' Performance. IEEE Transactions on Electron Devices, 2012, 59, 139-144.	1.6	13
21	High-k InGaAs metal-oxide-semiconductor field-effect-transistors with various barrier layer materials. Applied Physics Letters, 2011, 99, 033507.	1.5	19
22	InAs inserted InGaAs buried channel metal-oxide-semiconductor field-effect-transistors with atomic-layer-deposited gate dielectric. Applied Physics Letters, 2011, 98, .	1.5	36
23	Effect of indium concentration on InGaAs channel metal-oxide-semiconductor field-effect transistors with atomic layer deposited gate dielectric. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2011, 29, .	0.6	3
24	Impact of SF ₆ plasma treatment on performance of TaN/HfO ₂ /InP metal-oxide-semiconductor field-effect transistor. Applied Physics Letters, 2011, 98, 043506.	1.5	10
25	In _{0.7} Ga _{0.3} as Tunneling Field-Effect-Transistors with LaAlO ₃ and ZrO ₂ High-k Dielectrics. ECS Transactions, 2011, 41, 249-253.	0.3	1
26	Improving the on-current of In _{0.7} Ga _{0.3} As tunneling field-effect-transistors by p ⁺⁺ /n ⁺ tunneling junction. Applied Physics Letters, 2011, 98, .	1.5	26
27	Investigation of Surface Channel InGaAs MOSFETs with Al ₂ O ₃ and ZrO ₂ ALD Gate Dielectric. ECS Transactions, 2010, 33, 479-485.	0.3	5
28	Effects of barrier layers on device performance of high mobility In _{0.7} Ga _{0.3} As metal-oxide-semiconductor field-effect-transistors. Applied Physics Letters, 2010, 96, .	1.5	66
29	Fluorinated HfO ₂ gate dielectric engineering on In _{0.53} Ga _{0.47} As metal-oxide-semiconductor field-effect-transistors. Applied Physics Letters, 2010, 96, .	1.5	24
30	Effects of fluorine incorporation into HfO ₂ gate dielectrics on InP and In _{0.53} Ga _{0.47} As metal-oxide-semiconductor field-effect-transistors. Applied Physics Letters, 2010, 96, 253502.	1.5	24
31	Effects of InP barrier layer thicknesses and different ALD oxides on device performance of In _{0.7} Ga _{0.3} As MOSFETs. , 2010, , .		5
32	Improved electrical characteristics of TaN/Al ₂ O ₃ /In _{0.53} Ga _{0.47} As metal-oxide-semiconductor field-effect transistors by fluorine incorporation. Applied Physics Letters, 2009, 95, 013501.	1.5	33
33	Effects of gate-first and gate-last process on interface quality of In _{0.53} Ga _{0.47} As metal-oxide-semiconductor capacitors using atomic-layer-deposited Al ₂ O ₃ and HfO ₂ oxides. Applied Physics Letters, 2009, 95, .	1.5	42